## RELIABILITY REPORT

FOR

# MAX8863TEUK

PLASTIC ENCAPSULATED DEVICES

December 12, 2002

# **MAXIM INTEGRATED PRODUCTS**

120 SAN GABRIEL DR.

SUNNYVALE, CA 94086

Written by

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Bryan J. Preeshl Quality Assurance Executive Director

#### Conclusion

The MAX8863T successfully meets the quality and reliability standards required of all Maxim products. In addition, Maxim's continuous reliability monitoring program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards.

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## I. Device Description

#### A. General

The MAX8863T low-dropout linear regulator operates from a +2.5V to +6.5V input range and delivers up to 120mA. A PMOS pass transistor allows the low, 80µA supply current to remain independent of load, making this device ideal for battery-operated portable equipment such as cellular phones, cordless phones, and modems.

This device feature Dual Mode™ operation: its output voltage is preset at 3.15V or can be adjusted with an external resistor divider. Other features include low-power shutdown, short-circuit protection, thermal shutdown protection, and reverse battery protection. This device comes in a miniature 5-pin SOT23-5 package.

Pating

## B. Absolute Maximum Ratings

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<u>item</u>	Rating
V <sub>IN</sub> to GND	-7V to +7V
Output Short-Circuit Duration	Infinite
SET to GND	-0.3V to +7V
/SHDN to GND	-7V to +7V
/SHDN to IN	-7V to +0.3V
OUT to GND	-0.3V to (VIN + 0.3V)
Continuous Power Dissipation (TA = +70°C)	
5-Pin SOT23-5	571mW
Derates above +70°C	
5-Pin SOT23-5	7.1mW/°C
Operating Temperature Range	-40°C to +85°C
Junction Temperature	+150°C
Theta JA	140°C/Watt
Storage Temperature Range	-65°C to +160°C
Lead Temperature (soldering, 10sec)	+300°C

# II. Manufacturing Information

A. Description/Function: Low-Dropout, 120mA Linear Regulators

B. Process: S12 (Standard 1.2 micron silicon gate CMOS)

C. Number of Device Transistors: 148

D. Fabrication Location: California, USA

E. Assembly Location: Philippines, Thailand or Malaysia

F. Date of Initial Production: October, 1997

# III. Packaging Information

A. Package Type: 5-Pin SOT23

B. Lead Frame: Copper

C. Lead Finish: Solder Plate

D. Die Attach: Silver-filled Epoxy

E. Bondwire: Gold (1 mil dia.)

F. Mold Material: Epoxy with silica filler

G. Assembly Diagram: # 05-1701-0281

H. Flammability Rating: Class UL94-V0

I. Classification of Moisture Sensitivity

per JEDEC standard JESD22-112: Level 1

### IV. Die Information

A. Dimensions: 38 x 55 mils

B. Passivation: Si3N4/SiO2 (Silicon nitride/ Silicon dioxide)

C. Interconnect: Aluminum/Si (Si = 1%)

D. Backside Metallization: None

E. Minimum Metal Width: 1.2 microns (as drawn)

F. Minimum Metal Spacing: 1.2 microns (as drawn)

G. Bondpad Dimensions: 5 mil. Sq.

H. Isolation Dielectric: SiO<sub>2</sub>

I. Die Separation Method: Wafer Saw

## V. Quality Assurance Information

A. Quality Assurance Contacts: Jim Pedicord (Reliability Lab Manager)

Bryan Preeshl (Executive Director) Kenneth Huening (Vice President)

B. Outgoing Inspection Level: 0.1% for all electrical parameters guaranteed by the Datasheet.

0.1% For all Visual Defects.

C. Observed Outgoing Defect Rate: < 50 ppm

D. Sampling Plan: Mil-Std-105D

## VI. Reliability Evaluation

#### A. Accelerated Life Test

The results of the 135°C biased (static) life test are shown in **Table 1**. Using these results, the Failure Rate ( $\lambda$ ) is calculated as follows:

$$\lambda = \frac{1}{\text{MTTF}} = \frac{1.83}{192 \text{ x } 4389 \text{ x } 80 \text{ x } 2} \text{ (Chi square value for MTTF upper limit)}$$

$$\text{Temperature Acceleration factor assuming an activation energy of } 0.8\text{eV}$$

$$\lambda = 13.57 \times 10^{-9}$$

 $\lambda$  = 13.57 F.I.T. (60% confidence level @ 25°C)

This low failure rate represents data collected from Maxim's reliability monitor program. In addition to routine production Burn-In, Maxim pulls a sample from every fabrication process three times per week and subjects it to an extended Burn-In prior to shipment to ensure its reliability. The reliability control level for each lot to be shipped as standard product is  $\mathfrak B$  F.I.T. at a 60% confidence level, which equates to 3 failures in an 80 piece sample. Maxim performs failure analysis on any lot that exceeds this reliability control level. Attached Burn-In Schematic (Spec. # 06-5170) shows the static Burn-In circuit. Maxim also performs quarterly 1000 hour life test monitors. This data is published in the Product Reliability Report (RR-1M).

#### B. Moisture Resistance Tests

Maxim pulls pressure pot samples from every assembly process three times per week. Each lot sample must meet an LTPD = 20 or less before shipment as standard product. Additionally, the industry standard 85°C/85%RH testing is done per generic device/package family once a quarter.

#### C. E.S.D. and Latch-Up Testing

The PW84W die type has been found to have all pins able to withstand a transient pulse of  $\pm 1000$ V, per Mil-Std-883 Method 3015 (reference attached ESD Test Circuit). Latch-Up testing has shown that this device withstands a current of  $\pm 250$ mA and/or  $\pm 20$ V.

# Table 1 Reliability Evaluation Test Results

# MAX8863TEUK

TEST ITEM	TEST CONDITION	FAILURE IDENTIFICATION	PACKAGE	SAMPLE SIZE	NUMBER OF FAILURES
Static Life Test	t (Note 1)				
	Ta = 135°C Biased Time = 192 hrs.	DC Parameters & functionality		80	0
Moisture Testii	ng (Note 2)				
Pressure Pot	Ta = 121°C P = 15 psi. RH= 100% Time = 168hrs.	DC Parameters & functionality	SOT23	77	0
85/85	Ta = 85°C RH = 85% Biased Time = 1000hrs.	DC Parameters & functionality		77	0
Mechanical Str	ress (Note 2)				
Temperature Cycle	-65°C/150°C 1000 Cycles Method 1010	DC Parameters		77	0

Note 1: Life Test Data may represent plastic DIP qualification lots. Note 2: Generic Package/Process data

#### Attachment #1

TABLE II. Pin combination to be tested. 1/2/

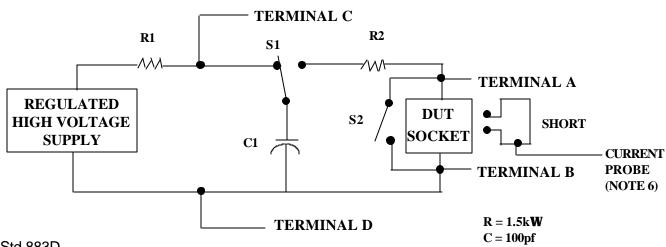
	Terminal A (Each pin individually connected to terminal A with the other floating)	Terminal B (The common combination of all like-named pins connected to terminal B)
1.	All pins except V <sub>PS1</sub> 3/	All V <sub>PS1</sub> pins
2.	All input and output pins	All other input-output pins

- 1/ Table II is restated in narrative form in 3.4 below.
- 2/ No connects are not to be tested.
- 3/ Repeat pin combination I for each named Power supply and for ground

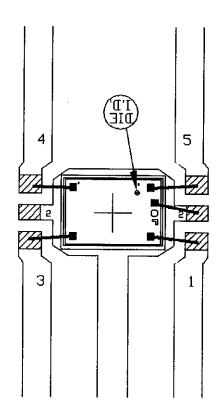
(e.g., where  $V_{PS1}$  is  $V_{DD}$ ,  $V_{CC}$ ,  $V_{SS}$ ,  $V_{BB}$ , GND,  $+V_{S}$ ,  $-V_{S}$ ,  $V_{REF}$ , etc).

# 3.4 Pin combinations to be tested.

- a. Each pin individually connected to terminal A with respect to the device ground pin(s) connected to terminal B. All pins except the one being tested and the ground pin(s) shall be open.
- b. Each pin individually connected to terminal A with respect to each different set of a combination of all named power supply pins (e.g., \( \lambda\_{S1} \), or \( \lambda\_{S2} \) or \( \lambda\_{S3} \) or \( \lambda\_{CC1} \), or \( \lambda\_{CC2} \)) connected to terminal B. All pins except the one being tested and the power supply pin or set of pins shall be open.
- c. Each input and each output individually connected to terminal A with respect to a combination of all the other input and output pins connected to terminal B. All pins except the input or output pin being tested and the combination of all the other input and output pins shall be open.



Mil Std 883D Method 3015.7 Notice 8



Ø- BONDING AREA

NOTE: CAVITY DOWN

PKG.CODE: U5-1	
CAV./PAD SIZE:	PKG.
64X45	DESIGN

APPROVALS

DATE

BUILDSHEET NUMBER: REV.

05-1701-0281

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